

# HN62408 Series — Preliminary

## 524288-Word × 16-Bit/1048576-Word × 8-Bit CMOS Mask Programmable ROM

HN62408 Series is a 8-Mbit CMOS mask-programmable ROM organized either as 524288-word x 16-Bit or as 1048576-Word x 8-Bit. It can be operated with a battery because of low power consumption. The large capacity of 8M bits is optimum for a kanji character generator.

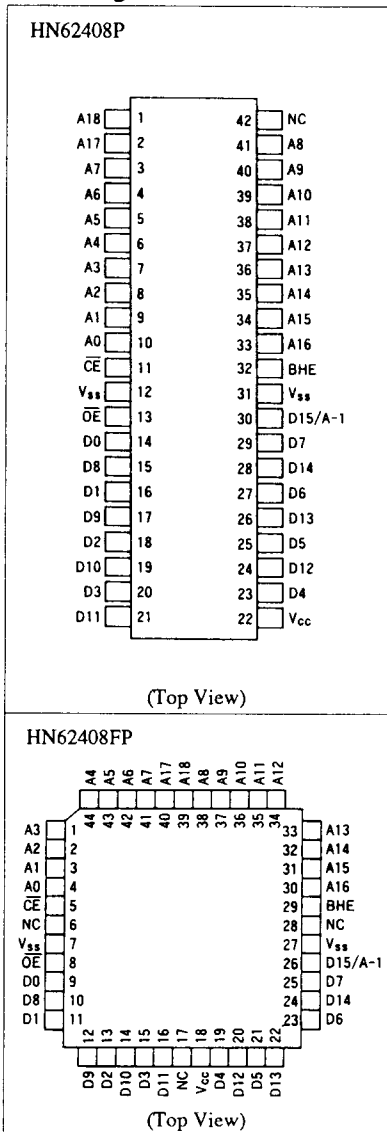
### Features

- Single 5 V
- Wired OR is permitted for the output in three states
- TTL compatible
- Address access time: 200 ns (max)
- Low power: Active 100 mW (typ)  
Standby 5  $\mu$ W (typ)
- Byte-Wide or Word-Wide Data Organization (switched by BHE terminal)

### Ordering Information

Type No.	Address Access Time	Package
HN62408P	200 ns	600 mil 42-pin plastic DIP
HN62408FP	200 ns	44-pin plastic QFP

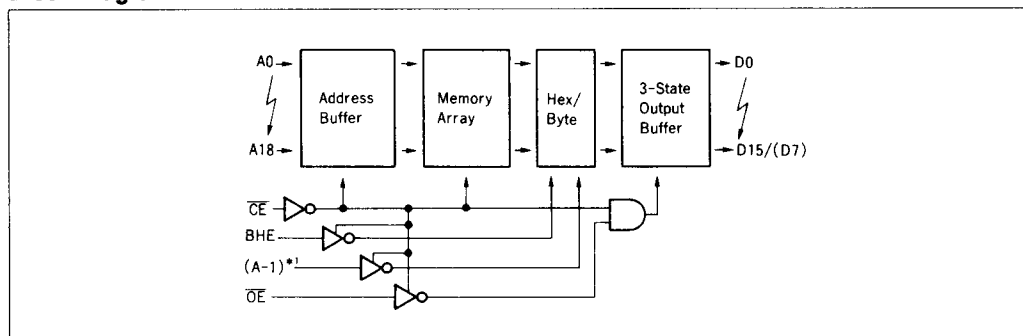
### Pin Arrangement



Note: The specifications of this device are subject to change without notice.  
Please contact your nearest Hitachi's Sale Dept. regarding specifications.



## Block Diagram



BHE =  $V_{\text{H}}$ : 16 bits (D15–D0)

BHE =  $V_{\text{L}}$ : 8 bits (D7–D0)

\*1: A-1 is least significant address input, and D14–D8 are of high impedance.

## Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Power supply voltage*1	$V_{\text{CC}}$	–0.3 to +7.0	V
Terminal voltage*1	$V_{\text{T}}$	–0.3 to $V_{\text{CC}} + 0.3$	V
Operating temperature	$T_{\text{opr}}$	0 to +70	°C
Storage temperature	$T_{\text{stg}}$	–55 to +125	°C
Bias temperature	$T_{\text{bias}}$	–20 to +85	°C

Note: \*1. With respect to  $V_{\text{SS}}$ .

## Recommended Operating Conditions ( $V_{\text{SS}} = 0 \text{ V}$ , $T_{\text{a}} = 0 \text{ to } +70^{\circ}\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit
Power supply voltage	$V_{\text{CC}}$	4.5	5.0	5.5	V
Input voltage	$V_{\text{H}}$	2.2	—	$V_{\text{CC}} + 0.3$	V
	$V_{\text{L}}$	–0.3	—	0.8	V

## DC Characteristics ( $V_{\text{CC}} = 5 \text{ V} \pm 10\%$ , $V_{\text{SS}} = 0 \text{ V}$ , $T_{\text{a}} = 0 \text{ to } +70^{\circ}\text{C}$ )

Item	Symbol	Min	Max	Unit	Test Conditions
Power supply current	Active $I_{\text{CC}}$	—	50	mA	$V_{\text{CC}} = 5.5 \text{ V}$ , $I_{\text{OUT}} = 0 \text{ mA}$ , $t_{\text{RC}} = \text{Min}$
	Standby $I_{\text{SB}}$	—	30	$\mu\text{A}$	$V_{\text{CC}} = 5.5 \text{ V}$ , $\overline{\text{CE}} \geq V_{\text{CC}} - 0.2 \text{ V}$
Input leak current	$ I_{\text{LI}} $	—	10	$\mu\text{A}$	$V_{\text{IN}} = 0 \text{ to } V_{\text{CC}}$
Output leak current	$ I_{\text{LO}} $	—	10	$\mu\text{A}$	$\overline{\text{CE}} = 2.2 \text{ V}$ , $V_{\text{OUT}} = 0 \text{ to } V_{\text{CC}}$
Output voltage	$V_{\text{OH}}$	2.4	—	V	$I_{\text{OH}} = -205 \mu\text{A}$
	$V_{\text{OL}}$	—	0.4	V	$I_{\text{OL}} = 1.6 \text{ mA}$



**Capacitance** ( $V_{CC} = 5\text{ V} \pm 10\%$ ,  $V_{SS} = 0\text{ V}$ ,  $T_a = 25^\circ\text{C}$ ,  $V_{in} = 0\text{ V}$ ,  $f = 1\text{ MHz}$ )

Item	Symbol	Min	Max	Unit
Input capacitance*1	Cin	—	15	pF
Output capacitance*1	Cout	—	15	pF

Note: \*1. This parameter is sampled and not 100% tested.

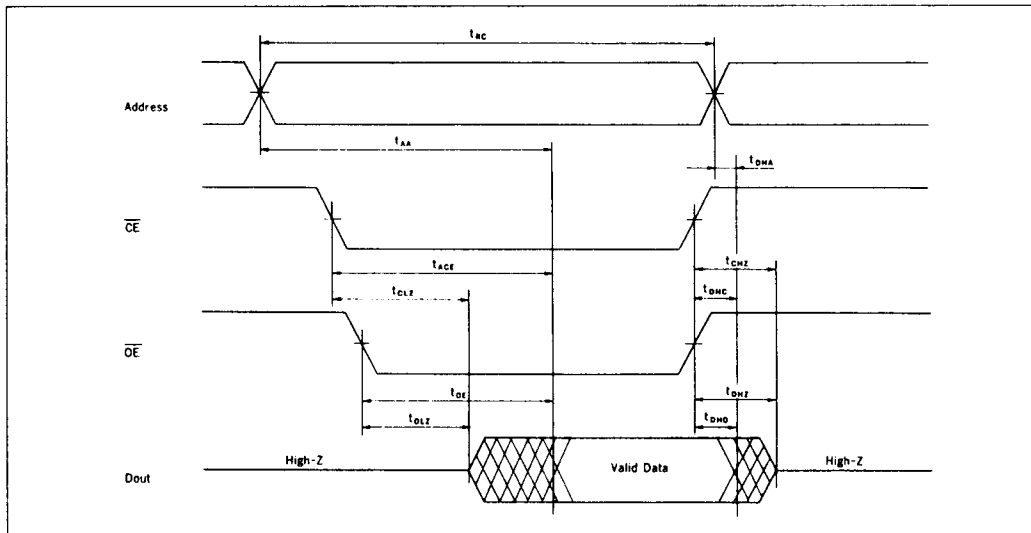
**AC Operating Characteristics** ( $V_{CC} = 5\text{ V} \pm 10\%$ ,  $V_{SS} = 0\text{ V}$ ,  $T_a = 0\text{ to }+70^\circ\text{C}$ )

**Test Conditions**

Input pulse level: 0.8 to 2.4 V      Output load: 1 TTL gate +  $C_L = 100\text{ pF}$   
I/O timing reference level: 1.5 V  
Input rise/fall time: 10 ns

Item	Symbol	Min	Max	Unit
Cycle time	tRC	200	—	ns
Address access time	tAA	—	200	ns
CE access time	tACE	—	200	ns
OE access time	tOE	—	100	ns
BHE access time	tBHE	—	200	ns
Output Hold Time from Address Change	tDHA	0	—	ns
Output Hold Time from CE	tDHC	0	—	ns
Output Hold Time from OE	tDHO	0	—	ns
Output Hold Time from BHE	tDHB	0	—	ns
CE to Output in High Z	tCHZ*1	—	70	ns
OE to Output in High Z	tOHZ*1	—	70	ns
BHE to Output in High Z	tBHZ*1	—	70	ns
CE to Output in Low Z	tCLZ	10	—	ns
OE to Output in Low Z	tOLZ	10	—	ns
BHE to Output in Low Z	tBLZ	10	—	ns

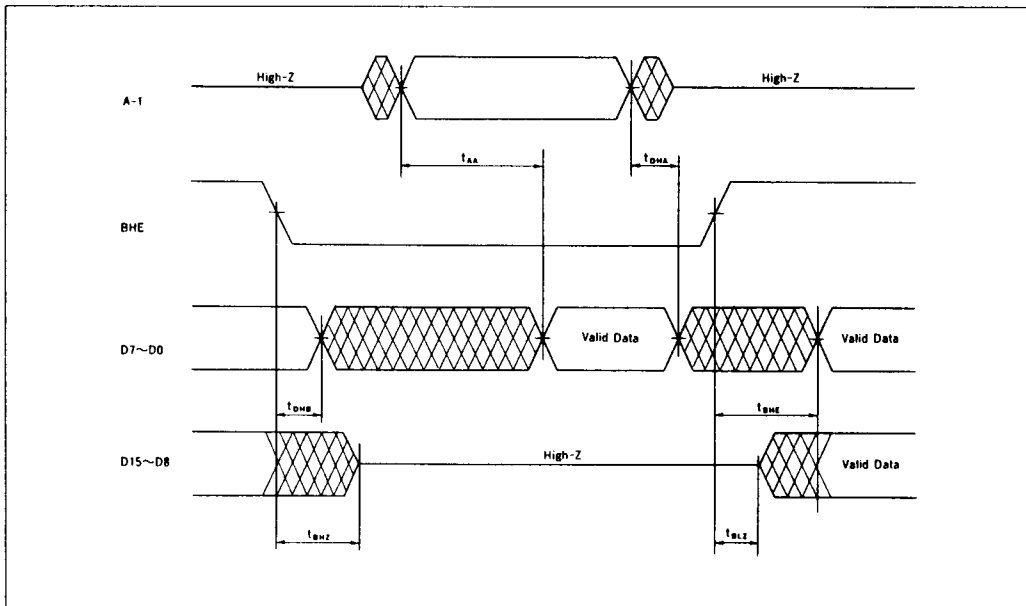
Note: \*1 tCHZ, tOHZ, and tBHZ define the time at which the output goes to the high impedance state and is not referenced to output voltage level.

**Timing Waveform****Word Mode (BHE = "V<sub>IH</sub>") or Byte Mode (BHE = "V<sub>IL</sub>")**

- Notes:
1.  $t_{DHA}$ ,  $t_{DHC}$ ,  $t_{DHO}$ ; Determined by whichever is faster.
  2.  $t_{AA}$ ,  $t_{ACE}$ ,  $t_{OE}$ ; Determined by whichever is slower.
  3.  $t_{CLZ}$ ,  $t_{OLZ}$ ; Determined by whichever is slower.



## Switching between Word Mode and Byte Mode



- Notes:
1.  $\overline{CE}$ ,  $\overline{OE}$  are of selected status. A18~A0 are fixed.
  2. D15/A-1 terminal is of output state when BHE =  $V_{IH}$ , CE and OE are of selected state.  
At this time, an input signal that is of the inverse phase to the output should not be impressed.